

Sushant Mittal

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/199971/publications.pdf>

Version: 2024-02-01

23
papers

132
citations

1307594

7
h-index

1588992

8
g-index

23
all docs

23
docs citations

23
times ranked

106
citing authors

#	ARTICLE	IF	CITATIONS
1	Analytical Estimation of Threshold Voltage Variability by Metal Gate Granularity in FinFET. IEEE Transactions on Electron Devices, 2017, 64, 3071-3076.	3.0	27
2	An Analytical Model to Estimate FinFET's V_{T} Distribution Due to Fin-Edge Roughness. IEEE Transactions on Electron Devices, 2016, 63, 1352-1358.	3.0	17
3	Analytical Model to Estimate FinFET's V_{T}^{ON} , V_{T}^{OFF} , SS, and V_{T} Distribution Due to FER. IEEE Transactions on Electron Devices, 2017, 64, 3489-3493.	3.0	13
4	Epitaxially Defined FinFET: Variability Resistant and High-Performance Technology. IEEE Transactions on Electron Devices, 2014, 61, 2711-2718.	3.0	11
5	An Analytical Model to Estimate V_{T} Distribution of Partially Correlated Fin Edges in FinFETs Due to Fin-Edge Roughness. IEEE Transactions on Electron Devices, 2017, 64, 1708-1715.	3.0	9
6	Impact of MOL/BEOL Air-Spacer on Parasitic Capacitance and Circuit Performance at 3 nm Node. , 2019, , .		9
7	The First Compact Model to Determine V_{T} Distribution for DG-FinFET Due to LER. IEEE Transactions on Electron Devices, 2018, 65, 4772-4779.	3.0	8
8	Statistical Variability Analysis of SRAM Cell for Emerging Transistor Technologies. IEEE Transactions on Electron Devices, 2016, 63, 3514-3520.	3.0	7
9	Epitaxially defined (ED) FinFET: to reduce V_{T} variability and enable multiple V_{T} , 2012, , .		5
10	Analytical modeling of metal gate granularity based threshold voltage variability in NWFET. Solid-State Electronics, 2018, 147, 26-34.	1.4	5
11	Epi defined (ED) FinFET: An alternate device architecture for high mobility Ge channel integration in PMOSFET. , 2013, , .		4
12	FinFET scaling rule based On variability considerations. , 2015, , .		4
13	A FinFET LER V_{T} variability estimation scheme with 300% efficiency improvement. , 2014, , .		3
14	Epitaxial rare earth oxide (EOx) FinFET: A variability-resistant Ge FinFET architecture with multi V_{T} , 2014, , .		2
15	Analytical modeling of metal gate granularity induced V_{T} variability in NWFETs. , 2016, , .		2
16	Selective Fin Trimming after Dummy Gate Removal as the Local Fin Width Scaling Approach for N5 and Beyond. , 2018, , .		2
17	Dopant deactivation: A new challenge in sub-20nm scaled FinFETs. , 2014, , .		1
18	A Bulk Planar SiGe Quantum-Well Based ZRAM with Low V_{t} Variability. , 2015, , .		1

#	ARTICLE	IF	CITATIONS
19	Highly-Doped Through-Contact Silicon Epi Design at 3 nm node. , 2019, , .		1
20	Via Size Optimization for Optimum Circuit Performance at 3 nm node. , 2020, , .		1
21	Epi Defined (ED) FinFET with dynamic threshold: Reduced V_{th} variability, enhanced performance, and a novel Multiple V_{th} . , 2013, , .		0
22	Cryogenic implantation for source/drain junctions in Ge p-channel (Fin)FETs. , 2014, , .		0
23	Scaling NC-FinFET to Sub-3 nm Nodes. , 2018, , .		0